AIDW40S65C5

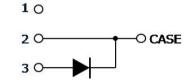


650V/40A Silicon Carbide Schottky Diode in TO247-3

Features

- Revolutionary semiconductor material Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Junction Temperature range from -40°C to 175°C
- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI





RoHS

Infineon

Potential Applications

- Traction inverter
- Booster / DCDC Converter
- On board Charger / PFC

Product Validation

"Qualified for Automotive Applications. Product Validation according to AEC-Q100/101"

Description

The 5th Generation CoolSiC[™] Automotive Schottky Diode represents Infineon leading edge technology for Silicon Carbide Schottky Barrier diodes. Thanks to a compact design and a technology based on thin wafers, this family of products shows improved efficiency over all load conditions resulting from both its thermal characteristics and low figure of merit (Qc x Vf). This product family has been designed to complement Infineon's IGBT and CoolMOS[™] portfolio. This ensures meeting the most stringent application requirements in the 650V voltage class.

🔁 Green

Product Information				
Ordering Code	AIDW40S65C5			
Marking	AD4065C5			
Package	PG-TO247-3-41			
SP Number	SP001725204			

Parameter	Value/Unit				
V _{DC,max}	650 V				
I _F ; T _C < 117 °C	40 A				
$Q_{\rm C}; V_{\rm R}$ = 400 V	56 nC				
E _C ; V _R = 400 V	12.9 µJ				
T _{j,max}	175 °C				

Pin	Definition
Pin 2, case	Cathode
Pin 3	Anode



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Maximum Ratings

1 Maximum Ratings

Table 1Maximum ratings1

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V _{RRM}	650	V
Continuous forward current for $R_{thJC,max}$ T _c = 117 °C, D=1	I _F	40	А
Surge non-repetitive forward current, sine halfwave T _c = 25°C, t _p =10ms T _c = 150°C, t _p =10ms	I _{F,SM}	182 153	A
Non-repetitive peak forward current T _c = 25°C, t _p =10μs	l _{F,max}	1432	A
$i^{2}t$ value T _c = 25°C, t _p =10ms T _c = 150°C, t _p =10ms	∫i ² dt	166 118	A ² s
Diode dv/dt ruggedness V _R =0480V	dv/dt	100	V/ns
Power dissipation T _c = 25°C	P _{tot}	183	W
Operating temperature	Tj	-40175	°C
Storage temperature	T _{stg}	-55150	°C
ESD Human body model, R= 1.5 kΩ, C = 100 pF Charged device model		8 2	kV
Soldering temperature, wavesoldering only allowed at leads, 1.6mm (0.063 in.) from case for 10 s	T _{sold}	260	°C
Mounting Torque (M3 and M4 screws)		70	Ncm



Thermal Characteristics

2 Thermal Characteristics

Table 2Thermal Characteristics1

Darameter	Symbol	Values			110:4	Noto /Toot oon didion
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
Thermal resistance, junction–case ²	R_{thJC}	-	0.6	0.8	K/W	
Thermal resistance, junction-ambient ²	R_{thJA}	-	-	62	K/W	



Electrical Characteristics

3 Electrical Characteristics

Table 3Static Characteristics

Parameter	Symbol	Values			Unit	Noto/Tost condition
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
DC blocking voltage	V _{DC}	650	-	-		T _j = 25°C, I _R = 0.12 mA
Diode forward voltage ³	V _F	-	1.5	1.7	v	T _j = 25°C, I _F = 40 A
		-	1.8	2.1		T _j = 150°C, I _F = 40 A
Reverse current	I _R	-	7	120		V _R = 650 V, T _j = 25 °C
		-	47	-	μA	V _R = 650 V, T _j = 150 °C

Table 4Dynamic Characteristics at Tj=25°C unless noted otherwise

Devementer	Symbol	Values			11	Noto (Tost condition
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
Total capacitive charge	Q _c	-	56	-	nC	$V_R = 400 \text{ V, } \text{di/dt} = 200 \text{ A/}\mu\text{s,}$ $I_F \le I_{F,MAX}, T_j = 150 \text{ °C}$
Total capacitance	С	-	1138	-	рF	V _R = 1 V, f = 1 MHz
		-	148	-		V _R = 300 V, f = 1 MHz
		-	145	-		V _R = 600 V, f = 1 MHz

Footnotes:

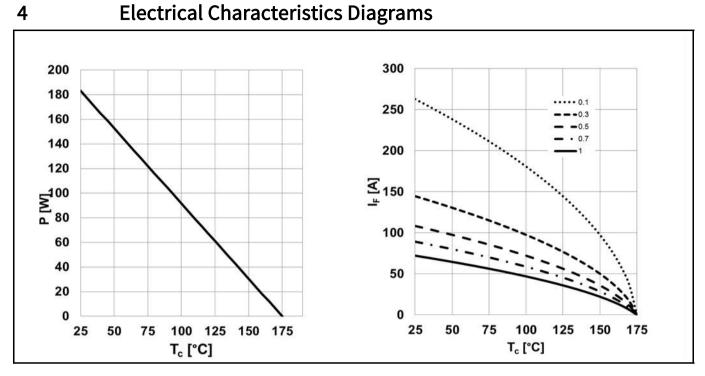
¹ The parameter is not subject to production test- verified by design/characterization.

² Rth, JC defined as per JESD-51-14. Rth, JA defined as per JESD-51-2.

³ Only the value at 25°C is subject to production test. The value at 150°C is only verified by design/characterization.

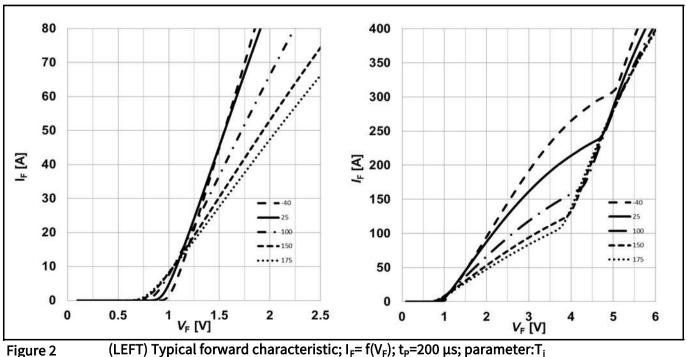


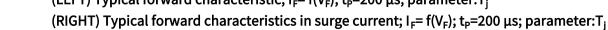
Electrical Characteristics Diagrams





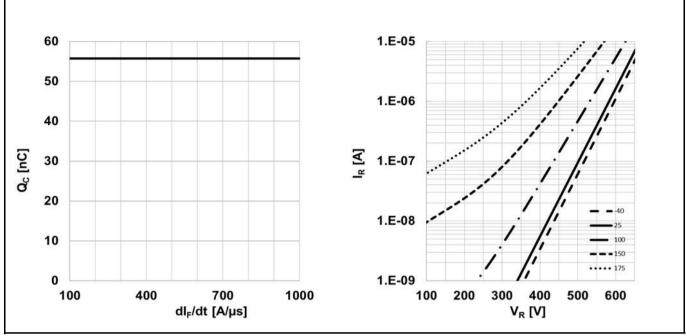
(LEFT) Power dissipation; $P_{tot} = f(T_C)$; $R_{thJC,max}$ (RIGHT) Diode forward current; $I_F = f(T_C)$; $T_J \le 175$ °C; $R_{thJC,max}$; parameter: D=duty cycle

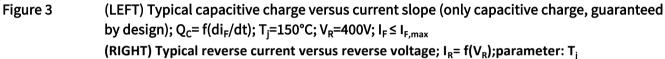






Electrical Characteristics Diagrams





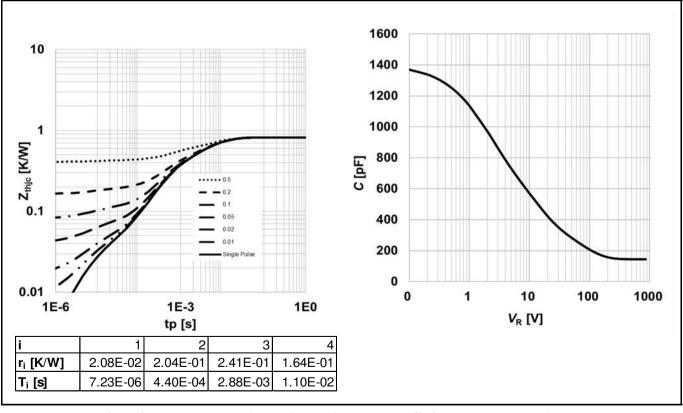


Figure 4

(LEFT) Max. Transient thermal impedance; $Z_{thJC} = f(t_P)$; parameter:D= t_P/T (RIGHT) Typ. Capacitance vs. Reverse voltage; C= $f(V_R)$; $T_i=25^{\circ}$ C; f=1 MHz



Electrical Characteristics Diagrams

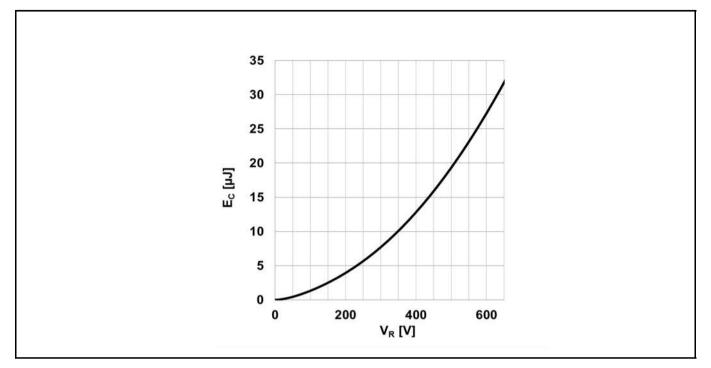
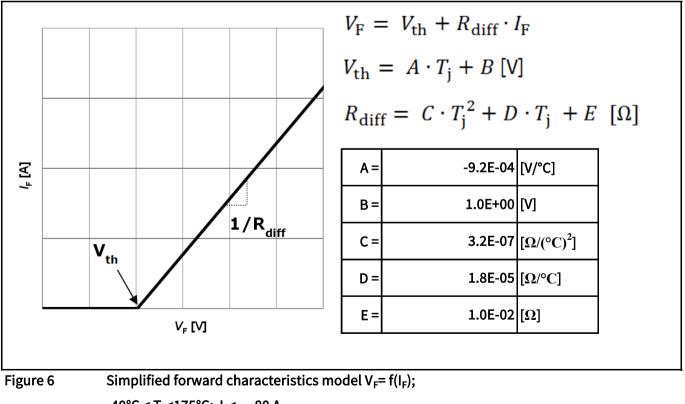


Figure 5 Typical capacitance stored energy; $E_{c} = f(V_{R})$



-40°C < T_i <175°C; I_F< 80 A



Package Outlines

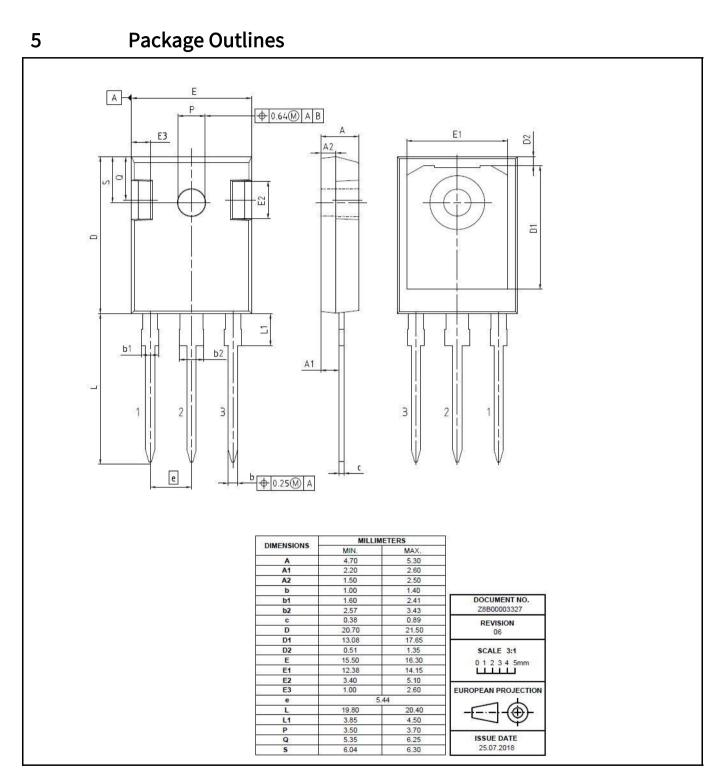


Figure 6

Package outline of PG-TO247-3-41 leaded (Dimensions in mm)



Revision History

Revision History

Document Version	Date of Release	Description of changes			
V3.0	26.11.2018	1st release of Data Sheet			



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